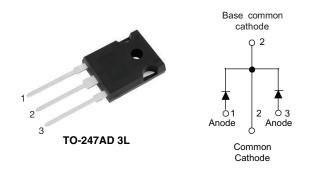
Vishay Semiconductors

650 V Power SiC Gen 3 Merged PIN Schottky Diode, 2 x 10 A



www.vishay.com

LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS							
l _F	2 x 10 A						
V _R	650 V						
V _F at I _F at 25 °C, typ.	1.3 V						
T _J max.	175 °C						
I _R at V _R at 175 °C	4.5 μA						
Q _C (V _R = 400 V)	29 nC						
Package	TO-247AD 3L						
Circuit configuration	Common cathode						

FEATURES

- Majority carrier diode using Schottky technology on SiC wide band gap material
- Improved V_F and efficiency by thin wafer RoHS COMPLIANT technology
- HALOGEN • Positive V_F temperature coefficient, for easy FREE paralleling
- Virtually no recovery tail and no switching losses
- Temperature invariant switching behavior
- 175 °C maximum operating junction temperature
- · MPS structure for high ruggedness to forward current surge events
- Meets JESD 201 class 1A whisker test
- Solder Bath temperature 275 °C maximum, 10 s per JESD 22-B106
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

DESCRIPTION / APPLICATIONS

Wide band gap SiC based 650 V Schottky diode, designed for high performance and ruggedness.

Optimum choice for high speed hard switching and efficient operation over a wide temperature range, it is also recommended for all applications suffering from Silicon ultrafast recovery behavior.

Typical applications include AC/DC PFC and DC/DC ultra high frequency output rectification in FBPS and LLC converters.

MECHANICAL DATA

Case: TO-247AD 3L

Molding compound meets UL 94 V-0 flammability rating Base P/N-M3 - halogen-free, RoHS-compliant Terminals: matte tin plated leads, solderable per

J-STD-002 and JESD 22-B102 Mounting torque: 10 in-lbs maximum

MAXIMUM RATINGS ($T_A = 25 \text{ °C}$ unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Peak repetitive reverse voltage	V _{RRM}		650	V				
Continuous forward current, per leg	I _F ⁽¹⁾	$I_{F}^{(1)} T_{C} = 146 \ ^{\circ}C \ (DC)$ $I_{F}^{(2)} T_{C} = 154 \ ^{\circ}C \ (DC)$		А				
Continuous forward current, per leg	I _F ⁽²⁾			~				
DC blocking voltage	V _{DC}		650	V				
Repetitive peak forward current	I _{FRM}	T_C = 25 °C, f = 50 Hz, square wave, DC = 25 $\%$	41					
Non repetitive peak forward aurge aurgent per leg	I _{FSM}	$T_{C} = 25 \text{ °C}, t_{p} = 10 \text{ ms}, \text{ half sine wave}$	60	А				
Non-repetitive peak forward surge current, per leg		T _C = 110 °C, t _p = 10 ms, half sine wave	58					
	P _{tot} ⁽¹⁾	$T_{C} = 25^{\circ}C$	79 W					
Dower dissipation per log		T _C = 110 °C	34	7 **				
Power dissipation, per leg	P _{tot} ⁽²⁾	$T_{C} = 25^{\circ}C$	107	w				
		T _C = 110 °C	46	vv				
l ² tualua par las	¢.2	$T_{C} = 25^{\circ}C$	18	A ² s				
l ² t value, per leg	∫i ² dt	T _C = 110 °C	17	A-S				
Operating junction and storage temperatures	T _J ⁽²⁾ , T _{Stg}		-55 to +175	°C				

Notes

⁽¹⁾ Based on maximum R_{th}

(2) Based on typical Rth

 $^{(3)}$ The heat generated must be less than the thermal conductivity from junction-to-ambient: $dP_D/dT_1 < 1/R_{0.IA}$

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ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)									
PARAMETER	TER SYMBOL TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS			
		I _F = 10 A	-	1.3	1.5				
Forward voltage, per leg	V _F	I _F = 10 A, T _J = 150 °C	-	1.46	1.85	V			
		I _F = 10 A, T _J = 175 °C	-	1.52	-				
		V _R = V _R rated	-	0.7	55				
Reverse leakage current, per leg	I _R	$V_R = V_R$ rated, $T_J = 150 \text{ °C}$	-	2.8	125	μA			
		$V_R = V_R$ rated, $T_J = 175 \ ^\circ C$	-	4.5	-				
Total capacitance, per leg	С	V _R = 1 V, f = 1 MHz	-	445	-	~ [
rotal capacitance, per leg	C	V _R = 400 V, f = 1 MHz	-	43	-	pF			
Total capacitive charge, per leg	Q _C	V _R = 400 V, f = 1 MHz	-	29	-	nC			

THERMAL - MECHANICAL SPECIFICATIONS ($T_A = 25 \text{ °C}$ unless otherwise specified)								
PARAMETER SYMBOL TEST CONDITIONS MIN. TYP. MAX. UNITS							UNITS	
The most uncitatence is motion to accord	per leg	Bth IC		-	1.4	1.9	°C/W	
Thermal resistance, junction-to-case	per device			-	0.8	1	°C/W	
Marking device				3C20CP07L				

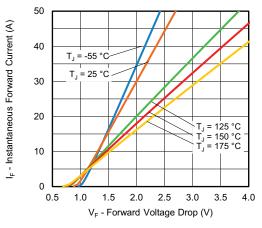


Fig. 1 - Typical Forward Voltage Drop Characteristics, Per Leg

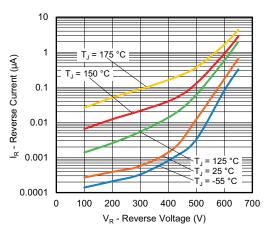


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage, Per Leg

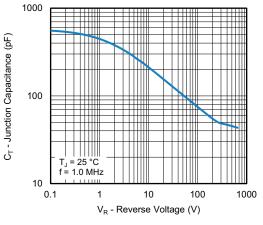


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage, Per Leg

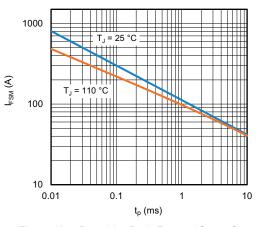


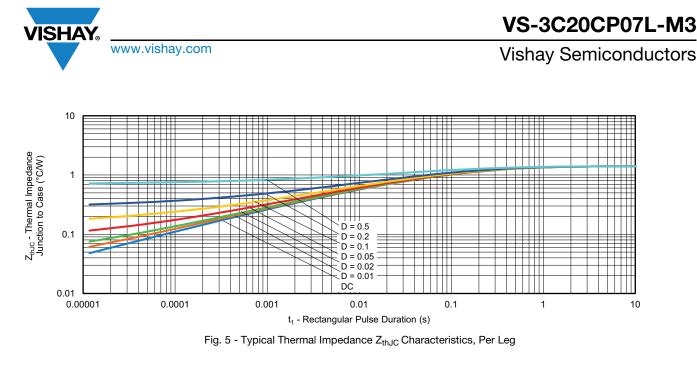
Fig. 4 - Non-Repetitive Peak Forward Surge Current vs. Pulse Duration, Per Leg (Square Wave)

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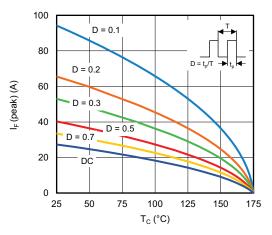


Fig. 6 - Peak Forward Current vs. Maximum Allowable Case Temperature, Per Leg

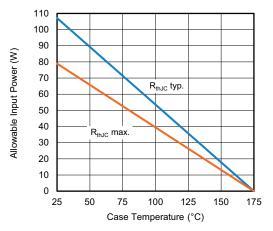


Fig. 7 - Forward Power Loss Characteristics, Per Leg

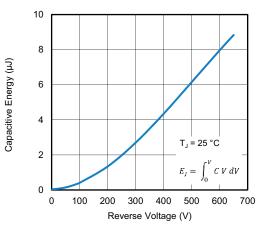


Fig. 8 - Typical Capacitive Energy vs. Reverse Voltage, Per Leg

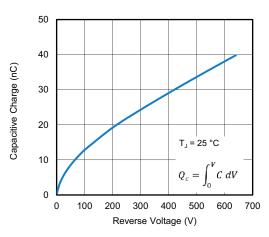


Fig. 9 - Typical Capacitive Charge vs. Reverse Voltage, Per Leg

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ORDERING INFORMATION TABLE

Device code	VS-	3C	20	с	Р	07	L	-M3
	1	2	3	4	5	6	7	8
	1	- Visl	nay Sem	nicondu	ctors pr	oduct		
	2	- 3C	= SiC di	iode, Ge	eneratio	n 3		
	3	- Cur	rent rati	ng (20 =	= 20 A)			
	4	- C =	commo	on catho	de			
	5	- P=	packag	e TO-24	17			
	6	- Vol	tage rati	ng: (07	= 650 V)		
	7	- L=	long lea	ld				
	8	- Env	vironmer	ntal digit	:			
		-M3	3 = halog	gen-free	e, RoHS	-compli	ant, and	d termir

ORDERING INFORMATION		
PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION
VS-3C20CP07L-M3	25/tube	Antistatic plastic tubes

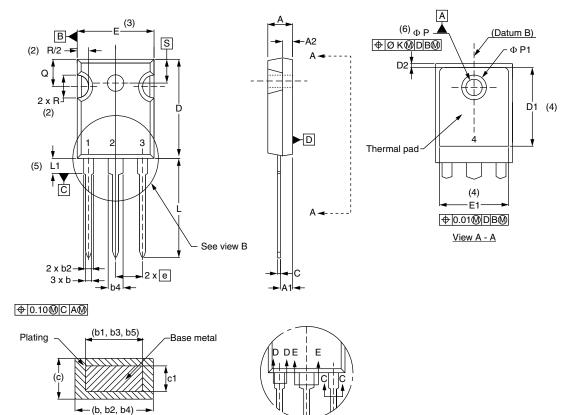
LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?95626
Part marking information	www.vishay.com/doc?95007



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TO-247AD 3L

DIMENSIONS in millimeters and inches



View B

SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STIVIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.65	5.31	0.183	0.209	
A1	2.21	2.59	0.087	0.102	
A2	1.50	2.49	0.059	0.098	
b	0.99	1.40	0.039	0.055	
b1	0.99	1.35	0.039	0.053	
b2	1.65	2.39	0.065	0.094	
b3	1.65	2.34	0.065	0.092	
b4	2.59	3.43	0.102	0.135	
b5	2.59	3.38	0.102	0.133	
с	0.38	0.89	0.015	0.035	
c1	0.38	0.84	0.015	0.033	
D	19.71	20.70	0.776	0.815	3
D1	13.08	-	0.515	-	4

(2, 52, 51) (4) Section C - C, D - D, E - E

SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STNIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
D2	0.51	1.30	0.020	0.051	
E	15.29	15.87	0.602	0.625	3
E1	13.46	-	0.53	-	
е	5.46	BSC	0.215	5 BSC	
ØК	0.2	0.254		0.010	
L	19.81	20.32	0.780	0.800	
L1	3.71	4.29	0.146	0.169	
ØР	3.56	3.66	0.14	0.144	
Ø P1	-	6.98	-	0.275	
Q	5.31	5.69	0.209	0.224	
R	4.52	5.49	0.178	0.216	
S	5.51 BSC		0.217 BSC		

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5M-1994

(2) Contour of slot optional

- ⁽³⁾ Dimension D and E do not include mold flash. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- ⁽⁵⁾ Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- ⁽⁷⁾ Outline conforms to JEDEC[®] outline TO-247 with exception of dimension A min., D, E min., Q min., S, and note 4

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